

Spin-polarized transport in $GaMnAs$ multilayers

L. Loureiro da Silva, M. A. Boselli, X. F. Wang and I. C. da Cunha Lima
Instituto de Física, Universidade do Estado do Rio de Janeiro
Rua São Francisco Xavier 524, 20.500-013 Rio de Janeiro, R.J., Brazil

and A. Ghazali
Groupe de Physique des Solides,
UMR 7588-CNRS, Universités Paris 7
et Paris 6
Tour 23, 2 Place Jussieu, F-75 251 Paris Cedex 05, France

The spin-dependent mobility for the lateral transport of the hole gas in a $GaMnAs/GaAs$ heterostructure containing several metallic-like ferromagnetic layers is calculated. The electronic structure is obtained self-consistently taking into account the direct Coulomb Hartree and exchange-correlation terms, besides the $sp-d$ exchange interaction with the Mn magnetic moments.

75.50.Pp, 75.70.Cn, 75.25.+x, 75.70.-i

Recent advances on growing $Ga_{1-x}Mn_xAs$ multilayers opened a wide range of interest in heterostructures of that Diluted Magnetic Semiconductor (DMS) [1,2], specially in spin-polarized transport due to potential applications in the area of quantum computers. Besides a magnetic impurity, Mn^{++} in this alloy is a strong p dopant. However, the density of carriers, as observed in measurements of the (anomalous) Hall resistance, is only a small fraction (of the order of 10%) of the Mn^{++} concentration, indicating that a major part of them remains neutral. The $sp-d$ exchange interaction of Ruderman-Kittel-Kasuya-Yosida (RKKY) type has been recognized as the main origin of the observed ferromagnetism in the metallic phase of III-V based DMS [3,4], and the possible magnetic ordering occurring in $Ga_{1-x}Mn_xAs$ heterostructures have been studied *via* Monte Carlo simulations on metallic samples [5]. Recently, a two component model has been suggested to contempt to the interplay of neutral and ionized Mn atoms in the magnetic interactions [6]. Chiba *et al* [7] investigated a trilayer structure and observed a ferromagnetic interaction, although weak, between two $GaMnAs$ ferromagnetic layers. More recently, ferromagnetic arrangements of $GaMnAs$ multilayers have been observed, forming a ferromagnetic superlattice [8]. Carriers, according to their polarization, are attracted or repelled by the magnetic layer. Therefore, the transport mean free path is expected to be different for each polarization. The aim of this work is to obtain the spin-polarized charge density, and to understand its effect on the spin-polarized transport in a model structure consisting of a sequence of $GaMnAs$ layers grown inside a thick non-magnetic $GaAs$ layer.

The spin-polarized electronic structure for holes is obtained self-consistently in the reciprocal space [9], taking

into account the hole-hole interaction as well as the hole interaction with the magnetic impurities through the contact potential:

$$U_{mag}(\mathbf{r}) = -I \sum_{i=1}^{N_i} \mathbf{s}(\mathbf{r}) \cdot \mathbf{S}(\mathbf{R}_i) \delta(\mathbf{r} - \mathbf{R}_i), \quad (1)$$

where I is the $p-d$ exchange coupling constant, $\mathbf{R}_i$ denotes the positions of the N_i impurities Mn , $\mathbf{S}(\mathbf{R}_i)$ is the (classical) spin of the impurity, and $\mathbf{s}$ is the spin of the hole. We assume the many layer magnetizations to be oriented in a single direction, each of them in their metallic and ferromagnetic phase. Thus, the spin of the hole is well defined in that direction, being polarized either up (parallel) or down (anti-parallel). When integrating the magnetic term in the Hamiltonian over $\mathbf{r}$, the magnetic impurities are assumed to be uniformly distributed in the $Ga_{1-x}Mn_xAs$ DMS layers, all of them in each magnetic layer j having the same magnetization, namely the thermal average magnetization $\langle \mathbf{M} \rangle_j$. Therefore,

$$I \int d^3r \exp[i(\mathbf{q} - \mathbf{q}') \cdot \mathbf{r}] \sum_{i=1}^{N_i} \mathbf{s}(\mathbf{r}) \cdot \mathbf{S}(\mathbf{R}_i) \delta(\mathbf{r} - \mathbf{R}_i) \simeq N_0 \beta x \frac{\sigma}{2} \sum_j \langle M \rangle_j F_{DMS}^j(q_z - q'_z) (2\pi)^3 \delta_2(\mathbf{q}_{\parallel} - \mathbf{q}'_{\parallel}), \quad (2)$$

where $\sigma = \pm 1$ for the hole spin orientation up (parallel) or down (anti-parallel) and δ_2 the two-dimensional δ -function in the q_{xy} -plane. As usual, $N_0 \beta = I/v_0$, where v_0 is the volume of the Mn^{++} ion. F_{DMS}^j is the integral performed on the z -coordinate across the j -th DMS layer:

$$F_{DMS}^j(q) \equiv \frac{1}{2\pi} \int_{DMS}^{(j)} dz \exp[iq \cdot z]. \quad (3)$$

A net Mn^{++} magnetization $\langle M \rangle_j$ polarizes the hole gas by introducing additional effective confining potentials given by

$$V_{mag}^{eff}(z) = -N_0 \beta x \frac{\sigma}{2} \sum_j \langle M \rangle_j g_j(z), \quad (4)$$

where $g_j(z) = 1$ if z lies inside the j -layer, and $g_j(z) = 0$ otherwise. With the use of

$$U_{eff}(q) = \frac{1}{2\pi} \int dz \exp[iqz][U_c(z) + V_{mag}^{eff}(z) + U_i(z)], \quad (5)$$

where $U_c(z)$ and $U_i(z)$ are, respectively, the confining and the hole-hole interaction potentials, one gets the one-dimensional secular equation in the q_z -direction:

$$\det \left\{ \left[\frac{\hbar^2 q^2}{2m^*} - E \right] \delta(q - q') + U_{eff}(q - q') \right\} = 0. \quad (6)$$

Each DMS layer works effectively as a barrier or a well for spins parallel or anti-parallel to the local average magnetization, depending on the sign of $N_0\beta$. For $x = 0.05$, and for $N_0\beta = -1.2\text{eV}$ [10] this corresponds to band offsets of $\pm 30 < M >_j \text{ meV}$. Throughout the calculation we made the hole density $p = 1. \times 10^{20} \text{ cm}^{-3}$, a fraction of roughly 10% of the Mn concentration, $T=0\text{K}$, and $< M >_j = 5/2$. Due to the high carrier density, several subbands are occupied.

The spin-polarized charge density distributions are shown in Fig. 1 for (a) one, (b) five, (c) eleven, and (d) seventeen DMS layers. We considered symmetric structures containing a number of $Ga_{0.95}Mn_{0.05}As$ layers of width $d = 20\text{\AA}$, separated by $20\text{\AA}$ width $GaAs$ layers, inside a $GaAs$ QW of width $400\text{\AA}$. A single $Ga_{0.95}Mn_{0.05}As$ layer occupying partially a $GaAs$ quantum well can be ferromagnetic for widths smaller than the case where the DMS occupy completely the quantum well, as it has been shown by Monte Carlo simulations [11]. However, a single layer of $20\text{\AA}$ is probably much too thin to be ferromagnetic. As the number of layers increases, the spin-polarized charge density distribution approaches that of a semiconductor superlattice with a band offset of $\pm 75\text{meV}$. Holes with the spin polarized parallel to the average magnetization occupy the interstitial regions between the magnetic layers, being repelled by the Mn layers due to the negative value of $N_0\beta$. Holes polarized anti-parallel to the average magnetization, on the contrary, are mostly located inside the DMS layers. Their density, however, is much lower than that of the anti-parallel spin holes, because the lowest occupied sub-bands are for this spin orientation. We expect the concentration of charge in the magnetic region to favor the ferromagnetic order of the system as compared to the single-layered structure, a fact that may be related with the recent experiments of Sadowski *et al.* [8]

Spin motion for carriers polarized parallel and anti-parallel to the equilibrium polarization in otherwise non-magnetic $GaAs$ samples has been predicted [12] to show a difference of an order of magnitude between the two speeds. The hole gas in these structures, when the spin-flip scattering is neglected, can be modeled by a two-carrier system. The corresponding Hamiltonian, with an electric field $\mathbf{E} = E\hat{x}$ applied in a direction parallel to the interfaces, is separated into center of mass (CM) and relative motions, in this case for each spin sub-system, each one with the instantaneous position of its CM, $\mathbf{R}_\sigma(t)$, and

its drift velocity expressed in terms of the spin-dependent mobility μ_σ , $\mathbf{v}_\sigma = \mu_\sigma \mathbf{E}$. The bare inter (and intra) sub-band impurity scattering potential $V_a^{n,n'}$ is:

$$V_a^{n,n'}(\mathbf{q}) = -\frac{Z_a e^2}{2\epsilon_0 \kappa} e^{-i\mathbf{q}\mathbf{R}_a} \int_{-\infty}^{\infty} dz \phi_n^*(z) \phi_{n'}(z) \frac{e^{-q|z-z_a|}}{q}, \quad (7)$$

where $\phi_m(z)$ is the hole wavefunction at the bottom of the sub-band m , which corresponds to a specific spin polarization. The frictional force due to the scattering by impurities balances the net effect of the applied electric field on the CM [13]:

$$f(v_\sigma) = \sum_{a,n,n',\mathbf{q}} |V_a^{n,n'}(\mathbf{q})|^2 q_x \Pi_2(n,n',q,q_x v_\sigma) = N_\sigma e E. \quad (8)$$

Here, the screening is included through the imaginary part of the polarization function $\Pi_2(n,n',q,\omega_\sigma)$, with the frequency argument $\omega_\sigma = q_x v_\sigma$, which can be approximated, in this simple case, by the unperturbed polarization [14].

Fig. (2) shows the spin polarized mobilities for a single $Ga_{0.95}Mn_{0.05}As$ layer in a $GaAs$ QW of width $120\text{\AA}$ as a function of the DMS layer width. As the width increases, corresponding to the increase of the effective magnetic well (barrier) width, holes with spins parallel (anti-parallel) are repelled from (attracted to) the region where the scatterers are located. An increasing number of occupied sub-bands corresponds to the anti-parallel polarization, reducing the parallel spin hole charge as compared to the anti-parallel one. It follows a decrease of the parallel polarization mobility, which is much more pronounced than that of the anti-parallel one. The mobility for a paramagnetic sample (at $T=100\text{K}$) is also included. It decreases as a function of the layer width almost in the same way as for the majority spins. Fig. (3) shows the mobilities for a series of structures in which a variable number of $Ga_{0.95}Mn_{0.05}As$ layers of width $20\text{\AA}$, separated by $20\text{\AA}$ width $GaAs$ layers, are symmetrically placed inside a $400\text{\AA}$ $GaAs$ QW, as in the calculation of the electronic structure of Fig.(1). We observe an oscillation of the mobilities for small number of layers, but the general trend is that above a certain number of layers the mobility of the anti-parallel polarization increase monotonically, while that of the parallel polarization decreases, reaching a plateau, the former being a factor of eight higher than the latter. Note that the paramagnetic mobility reaches a plateau just above a few layers.

We obtained a strongly spin-dependent mobility, with drift velocities differing by almost one order of magnitude, in agreement with other results [12]. This has an additional interest in what concerns the hole gas properties under an external magnetic field. On the other hand, from the theoretical point of view of non-linear transport, one could expect that a two-gas model presenting such a

difference in the drift velocities, as shown in this calculation, will generate higher order processes like a mutual Coulomb drag, and other non-equilibrium effects in the two spin-polarized electron gases.

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FIG. 3. Spin-polarized and paramagnetic mobilities versus the number of DMS layers for a multilayered structure of $20\text{\AA}$ width $Ga_{0.95}Mn_{0.05}As$ with a total width of $400\text{\AA}$.

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- [1] R. Fiederling, M. Keim, G. Reuscher, W. Ossau, G. Schmidt, A. Waag and L.W. Molenkamp, *Nature* **402**, 787 (1999).
 - [2] Y. Ohno, D.K. Young, B. Beschoten, F. Matsukura, H. Ohno and D.D. Awschalom, *Nature* **402**, 790 (1999).
 - [3] F. Matsukura, H. Ohno, A. Shen, and Y. Sugawara, *Phys. Rev. B* **57**, R2037 (1998).
 - [4] U. Gummich and I.C. da Cunha Lima, *Solid State Commun.* **76**, 831 (1990).
 - [5] M.A. Boselli, A. Ghazali, and I.C. da Cunha Lima, *Phys. Rev. B* **62**, 8895 (2000).
 - [6] Malcolm P. Kennet, Mona Berciu and R.N. Bhatt, *Cond-Mat* 0102315 (2001).
 - [7] D. Chiba, N. Akiba, F. Matsukura, Y. Ohno, and H. Ohno, *Appl. Phys. Lett.* **77**, 1873 (2000).
 - [8] J. Sadowski, K. Switek, R. Mathieu, P. Svedlindh, M. Karlsteen, J. Kansik, and L. Ilver (unpublished).
 - [9] A. Ghazali, I.C. da Cunha Lima, and M.A. Boselli, *Phys. Rev. B* **63**, 153305 (2001).
 - [10] J. Okabayashi, A. Kimura, O. Rader, T. Mizokawa, A. Fujimori, T. Hayashi, and M. Tanaka, *Phys. Rev. B* **58**, R4211 (1998).
 - [11] M.A. Boselli, I.C. da Cunha Lima, and A. Ghazali, *J. App. Phys.* **87**, 6439 (2000).
 - [12] Michael E. Flatté and Jeff M. Byers, *Phys. Rev. Lett.* **84**, 4220 (2000).
 - [13] X.L. Lei, and C.S. Ting, *Phys. Rev. B* **30**, 4809 (1984); **32**, 1112 (1985); X.L. Lei and N.J.M. Horing, *Int. J. Mod. Phys. B* **6**, 805 (1992); I.C. da Cunha Lima, X.F. Wang and X.L. Lei, *Phys. Rev. B* **55**, 10 681 (1997).
 - [14] G.D. Mahan, *Many-Particle Physics*, 2nd. Ed. (Plenum, New York, 1990).

FIG. 1. Spin-polarized charge density distributions for: (a) one, (b) five, (c) eleven, and (d) seventeen $Ga_{0.95}Mn_{0.05}As$ layers of $20\text{\AA}$, separated by $20\text{\AA}$ width $GaAs$ layers. Solid line for total charge density, dotted line for spin $\uparrow$ (parallel), dashed line for spin $\downarrow$ (anti-parallel).

FIG. 2. Spin-polarized and paramagnetic mobilities as functions of the magnetic layer width for a single layer of $Ga_{0.95}Mn_{0.05}As$ inside a $GaAs$ non-magnetic layer of width $120\text{\AA}$.





